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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q76253

Naoki OYANAGI

Appln. No.: Based on PCT/JP2004/008681

Confirmation No.: Unknown

Group Art Unit: Unknown

Filed: December 15, 2005

Examiner: Unknown

METHOD FOR GROWTH OF SILICON CARBIDE SINGLE CRYSTAL, SILICON

CARBIDE SEED CRYSTAL, AND SILICON CARBIDE SINGLE CRYSTAL

PRELIMINARY AMENDMENT

MAIL STOP AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Prior to examination, please amend the above-identified application as follows on the accompanying pages.

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